

GY Dual/Quad Low Noise, High Speed Precision Op Amps

FEATURES

100% Tested Low Voltage Noise	2.7nV/√Hz Typ
	4.2nV/√Hz Max
■ Slew Rate	4.5V/μs Typ
Gain Bandwidth Product	12.5MHz Typ
 Offset Voltage, Prime Grade 	70μV Max
Low Grade	100μV Max
High Voltage Gain	5 Million Min
Supply Current Per Amplifier	2.75mA Max
 Common Mode Rejection 	112dB Min
 Power Supply Rejection 	116dB Min
Available in 8-Pin SO Package	

APPLICATIONS

- Two and Three Op Amp Instrumentation Amplifiers
- Low Noise Signal Processing
- Active Filters
- Microvolt Accuracy Threshold Detection
- Strain Gauge Amplifiers
- Direct Coupled Audio Gain Stages
- Tape Head Preamplifiers
- Infrared Detectors

DESCRIPTION

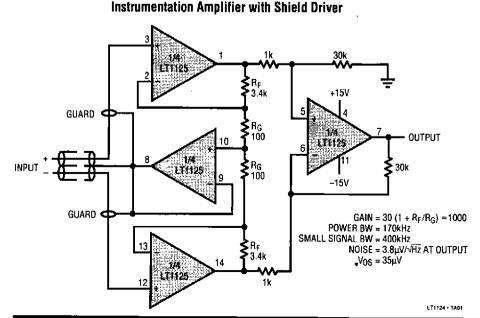
The LT1124 dual and LT1125 quad are high performance op amps that offer higher gain, slew rate, and bandwidth than the industry standard OP-27 and competing OP-270/OP-470 op amps. In addition, the LT1124/LT1125 have lower I_B and I_{OS} than the OP-27; lower V_{OS} and noise than the OP-270/OP-470.

In the design, processing, and testing of the device, particular attention has been paid to the optimization of the entire distribution of several key parameters. Slew rate, gain bandwidth, and 1kHz noise are 100% tested for each individual amplifier. Consequently, the specifications of even the lowest cost grades (the LT1124C and the LT1125C) have been spectacularly improved compared to equivalent grades of competing amplifiers.

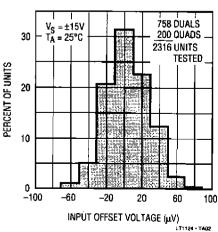
Power consumption of the LT1124 is one half of two OP-27s. Low power and high performance in an 8-pin SO package make the LT1124 a first choice for surface mounted systems and where board space is restricted.

For a decompensated version of these devices, with three times higher slew rate and bandwidth, please see the LT1126/LT1127 data sheet.

Protected by U.S. patents 4,775,884 and 4,837,496.



Input Offset Voltage Distribution (All Packages, LT1124 and LT1125)



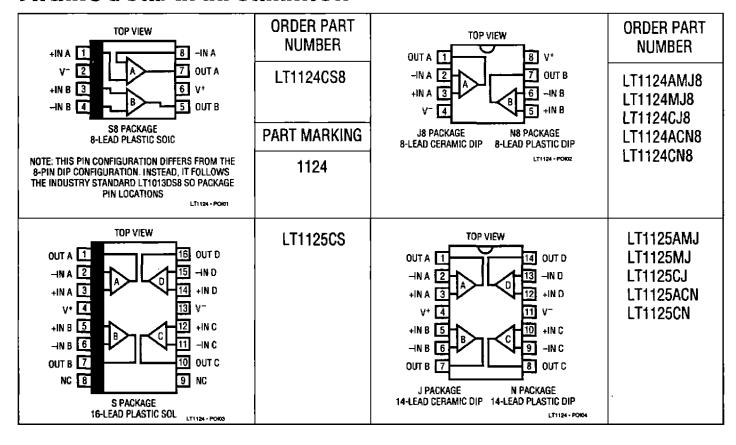
ABSOLUTE MAXIMUM RATINGS

2

Supply Voltage	<u>+</u> 22V
Input Voltages	Equal to Supply Voltage
Output Short Circuit Duration	Indefinite
Differential Input Current (Note	5)±25mA
Lead Temperature (Soldering, 1	•

Operating Temperature Range	
LT1124AM/LT1124M	
LT1125AM/LT1125M	55°C to 125°C
LT1124AC/LT1124C	
LT1125AC/LT1125C	40°C to 85°C
Storage Temperature Range	
All Grades	65°C to 150°C

PACKAGE/ORDER INFORMATION



ELECTRICAL CHARACTERISTICS $V_8 = \pm 15V$, $T_A = 25^{\circ}C$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS (Note 1)	LT1124AM/AC LT1125AM/AC MIN TYP MA)	LT1124M/C LT1125M/C MIN TYP MAX	UNITS
Vos	Input Offset Voltage	LT1124	20 70	25 100	μV
		LT1125	25 90	30 140	μV
ΔV _{OS} ΔTime	Long Term Input Offset Voltage Stability		0.3	0.3	μV/Mo
los	Input Offset Current	LT1124 LT1125	5 15 6 20	6 20 7 30	nA nA



ELECTRICAL CHARACTERISTICS $v_s = \pm 15 V$, $T_A = 25^{\circ}C$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS (Note 1)	LT1124AM/AC LT1125AM/AC MIN TYP MAX	LT1124M/C LT1125M/C MIN TYP MAX	UNITS
В	Input Bias Current		±7 ±20	±8 ±30	nΑ
en	Input Noise Voltage	0.1Hz to 10Hz (Notes 7 and 8)	70 200	70	nVp-p
	Input Noise Voltage Density	f _O = 10Hz (Note 3) f _O = 1000Hz (Note 2)	3.0 5.5 2.7 4.2	3.0 5.5 2.7 4.2	nV/√Hz nV/√Hz
in	Input Noise Current Density	f ₀ = 10Hz f ₀ = 1000Hz	1.3 0.3	1.3 0.3	pA/√Hz pA/√Hz
V _{CM}	Input Voltage Range		± 12.0 ± 12.8	± 12.0 ± 12.8	٧
CMRR	Common Mode Rejection Ratio	V _{CM} = ±12V	112 126	106 124	dB
PSRR	Power Supply Rejection Ratio	V _S = ±4V to ±18V	116 126	110 124	d₿
Ã _{VOL}	Large Signal Voltage Gain	$R_L \ge 10k\Omega$, $V_0 = \pm 10V$ $R_L \ge 2k\Omega$, $V_0 = \pm 10V$	5.0 17.0 2.0 4.0	3.0 15.0 1.5 3.0	V/μV V/μV
V _{OUT}	Maximum Output Voltage Swing	$R_L \ge 2k\Omega$	±13.0 ±13.8	± 12.5 ± 13.8	٧
SR	Slew Rate	$R_L \ge 2k\Omega$ (Notes 2 and 6)	3.0 4.5	2.7 4.5	V/µs
GBW	Gain-Bandwidth Product	f _O =100kHz (Note 2)	9.0 12.5	8.0 12.5	MHz
Z ₀	Open Loop Output Resistance	$V_0 = 0$, $I_0 = 0$	75	75	Ω
Is	Supply Current Per Amplifier		2.3 2.75	2.3 2.75	mA
	Channel Separation	$f \le 10$ Hz (Note 8) $V_0 = \pm 10$ V, $R_L = 2$ k Ω	134 150	130 150	dB

ELECTRICAL CHARACTERISTICS $V_S = \pm 15V, -55^{\circ}C \le T_A \le 125^{\circ}C$, unless otherwise noted.

					124A 125A		_	Γ1124N Γ1125N		
SYMBOL	PARAMETER	CONDITIONS (Note 1)		MIN	TYP	MAX	MIN	TYP	MAX	UNITS
V_{OS}	Input Offset Voltage	LT1124	•		50	170		60	250	μV
		LT1125	•		55	190		70	290	μV
ΔV _{OS} ΔTemp	Average Input Offset Voltage Drift	(Note 4)	•		0.3	1.0		0.4	1.5	μV/°C
-	Innut Officet Courant	171104			10					
los	Input Offset Current	LT1124 LT1125			18 18	45 55		20 20	60 70	nA
	In a Bin Comment	LITIZO								An
IB	Input Bias Current		•		± 18	± 55		±20	±70	пА
V _{CM}	Input Voltage Range		•	±11.3	± 12		± 11.3	± 12		V
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 11.3V$	•	106	122		100	120		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 4V$ to $\pm 18V$	•	110	122		104	120	_	dB
Avol	Large Signal Voltage Gain	$R_L \ge 10k\Omega$, $V_0 = \pm 10V$	•	3.0	10.0		2.0	10.0)	V/µV
		$R_L \ge 2k\Omega$, $V_0 = \pm 10V$	•	1.0	3.0		0.7	2.0		٧/μ٧
V _{OUT}	Maximum Output Voltage Swing	$R_L \ge 2k\Omega$	•	± 12.5	± 13.6		± 12.0	± 13.6	3	V
SR	Slew Rate	$R_L \ge 2k\Omega$ (Notes 2 and 6)	•	2.3	3.8		2.0	3.8		V/µs
Is	Supply Current Per Amplifier		•		2.5	3.25		2.5	3.25	mΑ

ELECTRICAL CHARACTERISTICS $v_s = \pm 15 V$, $0^{\circ}C \le T_A \le 70^{\circ}C$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS (Note 1)	_	LT1124A LT1125A Min Typ		LT1124 LT1125 MIN TYP	-	UNITS
Vos	Input Offset Voltage	LT1124	•	35	120	45	170	μV
		LT1125	•	40	140	50	210	μV
ΔV _{OS}	Average Input Offset Voltage Drift	(Note 4)	•	0.3	1.0	0.4	1.5	µV/°C
ΔTemp								
Ios	Input Offset Current	LT1124	•	6	25	7	35	nA
		LT1125	•	7	35	8	45	nA
l _B	Input Bias Current		•	±8	± 35	±9	± 45	nA
V _{CM}	Input Voltage Range		•	± 11.5 ± 12.4	1	±11.5 ±12.	4	V
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 11.5V$	•	109 125		102 122	!	dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 4V$ to $\pm 18V$	•	112 125		107 122	!	d8
A _{VOL}	Large Signal Voltage Gain	$R_L \ge 10k\Omega$, $V_0 = \pm 10V$	•	4.0 15.0)	2.5 14.	0	V/µV
		$R_L \ge 2k\Omega$, $V_0 = \pm 10V$	•	1.5 3.5		1.0 2.5		V/μV
V _{OUT}	Maximum Output Voltage Swing	$R_L \ge 2k\Omega$	•	± 12.5 ± 13.7	7	± 12.0 ± 13.	7	V
SR	Slew Rate	$R_L \ge 2k\Omega$ (Notes 2 and 6)	•	2.6 4.0		2.4 4.0		V/µs
Is	Supply Current Per Amplifier		•	2.4	3.0	2.4	3.0	mA

ELECTRICAL CHARACTERISTICS $V_8 = \pm 15 V, -40 ^{\circ} C \le T_A \le 85 ^{\circ} C,$ unless otherwise noted. (Note 9)

SYMBOL	PARAMETER	CONDITIONS (Note 1)		LT1124 LT1125 MIN TYF	AC		11240 11250 TYP		UNITS
			1.			MIN			
v_{os}	Input Offset Voltage	LT1124	•	40	140		50	200	μV
		LT1125	•	45	160		55	240	μV
ΔV_{OS}	Average Input Offset Voltage Drift		•	0.3	1.0		0.4	1.5	μV/°C
ΔTemp									
los	Input Offset Current	LT1124	•	15	40		17	55	nA
		LT1125	•	15	50		17	65	nA
l _B	Input Bias Current		•	± 15	± 50		± 17	± 65	nA
V _{CM}	Input Voltage Range		•	± 11.4 ± 12.	2	±11.4	± 12.2	<u>.</u>	V
CMRR	Common Mode Rejection Ratio	V _{CM} = ±11.4V	•	107 124	4	101	121		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 4V \text{ to } \pm 18V$	•	111 12	4	106	121		dB
A _{VOL}	Large Signal Voltage Gain	$R_L \ge 10k\Omega$, $V_0 = \pm 10V$	•	3.5 12.	0	2.2	12.0)	V/µV
		$R_L \ge 2k\Omega$, $V_0 = \pm 10V$	•	1.2 3.2		0.8	2.3		V/μV
V _{OUT}	Maximum Output Voltage Swing	$R_L \ge 2k\Omega$	•	± 12.5 ± 13.	6	± 12.0	± 13.6	6	V
SR	Slew Rate	$R_L \ge 2k\Omega$ (Note 6)	•	2.4 3.9)	2.1	3.9		V/μs
Is	Supply Current Per Amplifier		•	2.4	3.25	-	2.4	3.25	mA

The • denotes the specifications which apply over the full operating temperature range.

Note 1: Typical parameters are defined as the 60% yield of parameter distributions of individual amplifiers; i.e., out of 100 LT1125's (or 100 LT1124's) typically 240 op amps (or 120) will be better than the indicated specification.

Note 2: This parameter is 100% tested for each individual amplifier.

Note 3: This parameter is sample tested only.

Note 4: This parameter is not 100% tested.

Note 5: The inputs are protected by back-to-back diodes. Current limiting resistors are not used in order to achieve low noise. If differential input voltage exceeds ±1.4V, the input current should be limited to 25mA.

Note 6: Slew rate is measured in $A_V = -1$; input signal is $\pm 7.5V$, output measured at $\pm 2.5V$.

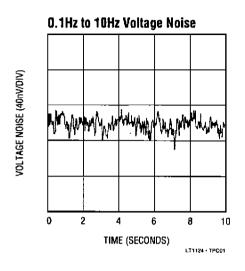
Note 7: 0.1Hz to 10Hz noise can be inferred from the 10Hz noise voltage density test. See the test circuit and frequency response curve for 0.1Hz to 10Hz tester in the Applications Information section of the LT1007 or LT1028 data sheets.

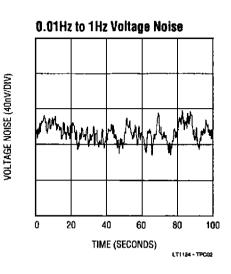
Note 8: This parameter is guaranteed but not tested.

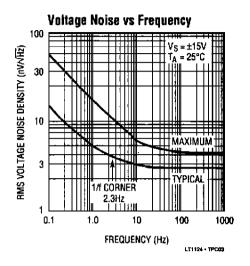
Note 9: The LT1124/LT1125 are not tested and are not quality-assurance-sampled at -40° C and at 85°C. These specifications are guaranteed by design, correlation and/or inference from -55° C, 0° C, 25° C, 70° C and/or 125°C tests.

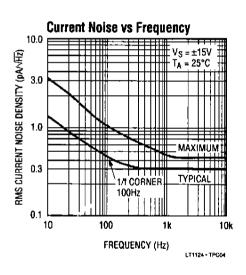


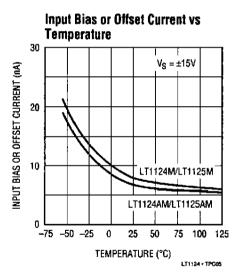
TYPICAL PERFORMANCE CHARACTERISTICS

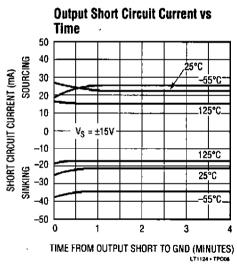


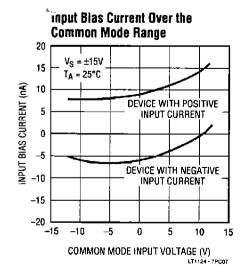


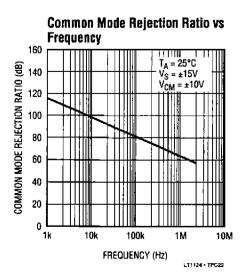


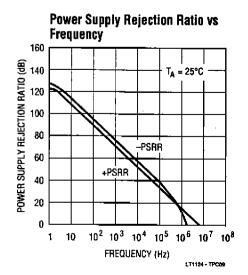






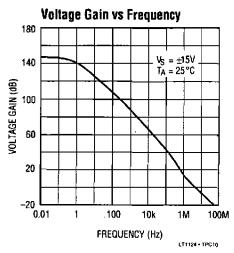


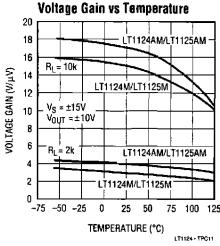




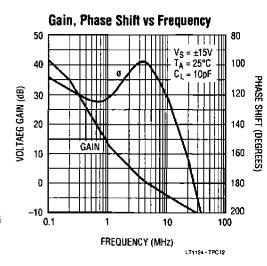


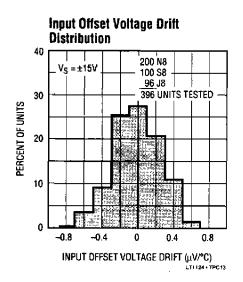
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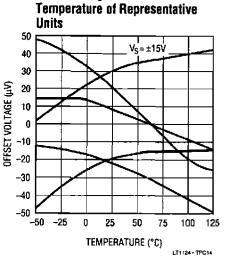


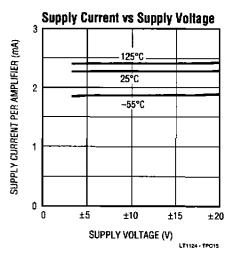


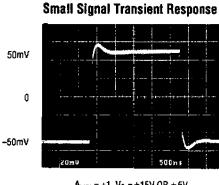
Offset Voltage Drift with

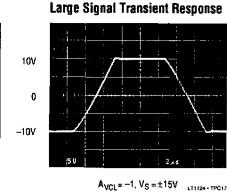


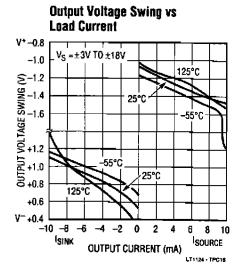




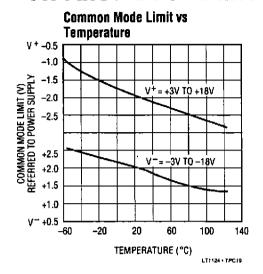


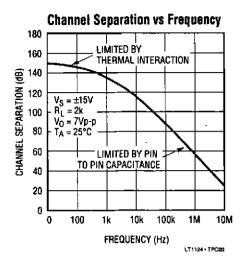


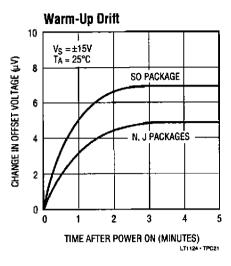




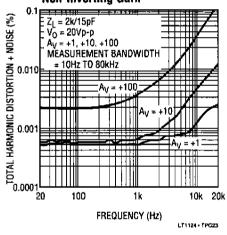
TYPICAL PERFORMANCE CHARACTERISTICS



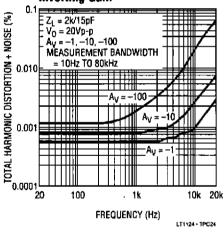




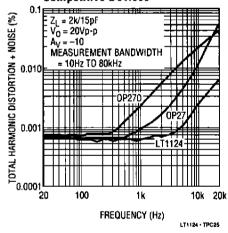
Total Harmonic Distortion and Noise vs Frequency for Non-Inverting Gain



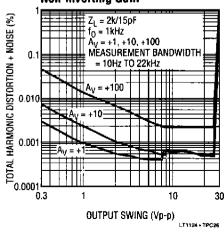




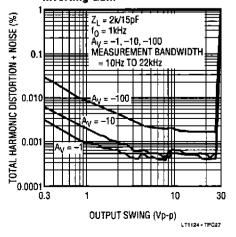
Total Harmonic Distortion and Noise vs Frequency for Competitive Devices



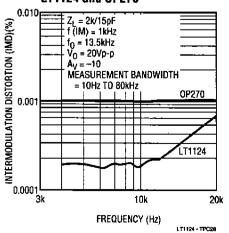
Total Harmonic Distortion and Noise vs Output Amplitude for Non-Inverting Gain



Total Harmonic Distortion and Noise vs Output Amplitude for Inverting Gain



Intermodulation Distortion (CCIF Method)* vs Frequency LT1124 and OP270



^{*}See LT1115 data sheet for definition of CCIF testing

APPLICATIONS INFORMATION

The LT1124 may be inserted directly into OP-270 sockets. The LT1125 plugs into OP-470 sockets. Of course, all standard dual and quad bipolar op amps can also be replaced by these devices.

Matching Specifications

In many applications the performance of a system depends on the matching between two op amps, rather than the individual characteristics of the two devices. The three op amp instrumentation amplifier configuration shown in this data sheet is an example. Matching characteristics are not 100% tested on the LT1124/LT1125.

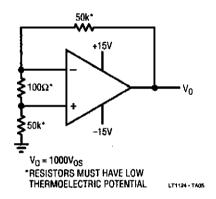
Some specifications are guaranteed by definition. For example, $70\mu V$ maximum offset voltage implies that mismatch cannot be more than $140\mu V$. 112dB (= $2.5\mu V/V$) CMRR means that worst case CMRR match is 106dB ($5\mu V/V$). However, the following table can be used to estimate the expected matching performance between the two sides of the LT1124, and between amplifiers A and D, and between amplifiers B and C of the LT1125.

Offset Voltage and Drift

Thermocouple effects, caused by temperature gradients across dissimilar metals at the contacts to the input terminals, can exceed the inherent drift of the amplifier unless proper care is exercised. Air currents should be minimized, package leads should be short, the two input leads should be close together and maintained at the same temperature.

The circuit shown to measure offset voltage is also used as the burn-in configuration for the LT1124/LT1125, with the supply voltages increased to $\pm 16V$.

Test Circuit for Offset Voltage and Offset Voltage Drift with Temperature



Expected Match

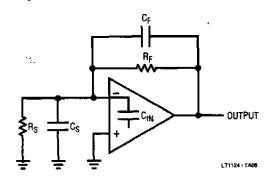
PARAMETER			IAM/AC 5AM/AC		LT1124M/C LT1125M/C		
		50% YIELD	98% YIELD	50% YIELD	98% YIELD	UNITS	
V _{OS} Match, ΔV _{OS}	LT1124 LT1125	20 30	110 150	30 50	130 180	μV μV	
Temperature Coeffic	cient Match	0.35	1.0	0.5	1.5	μV/°C	
Average Non-Invert	ing l ₈	6	18	7	25	nA	
Match of Non-Inver	ting I _B	7	22	8	30	nA	
CMRR Match		126	115	123	112	dB	
PSRR Match		127	118	127	114	dB	



APPLICATIONS INFORMATION

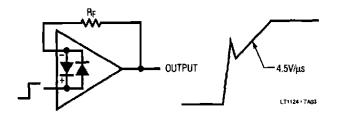
High Speed Operation

When the feedback around the op amp is resistive (R_F) , a pole will be created with R_F , the source resistance and capacitance (R_S, C_S) , and the amplifier input capacitance $(C_{IN} \approx 2pF)$. In low closed loop gain configurations and with R_S and R_F in the kilohm range, this pole can create excess phase shift and even oscillation. A small capacitor (C_F) in parallel with R_F eliminates this problem. With R_S $(C_S + C_{IN}) = R_F C_F$, the effect of the feedback pole is completely removed.



Unity Gain Buffer Applications

When $R_F \le 100\Omega$ and the input is driven with a fast, large signal pulse (>1V), the output waveform will look as shown.



During the fast feedthrough-like portion of the output, the input protection diodes effectively short the output to the input and a current, limited only by the output short circuit protection, will be drawn by the signal generator. With $R_F \geq 500\Omega$, the output is capable of handling the current requirements ($I_L \leq 20 \text{mA}$ at 10V) and the amplifier stays in its active mode and a smooth transition will occur.

Noise Testing

Each individual amplifier is tested to $4.2nV/\sqrt{Hz}$ voltage noise; i.e., for the LT1124 two tests, for the LT1125 four tests are performed. Noise testing for competing multiple op amps, if done at all, may be sample tested or tested using the circuit below.

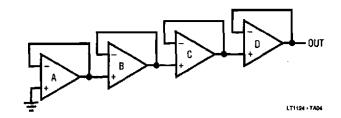
$$e_{n \text{ OUT}} = \sqrt{(e_{nA})^2 + (e_{nB})^2 + (e_{nC})^2 + (e_{nD})^2}$$

If the LT1125 were tested this way, the noise limit would be $\sqrt{4} \times (4.2 \text{nV}/\sqrt{\text{Hz}})^2 = 8.4 \text{nV}/\sqrt{\text{Hz}}$. But is this an effective screen? What if three of the four amplifiers are at a typical $2.7 \text{nV}/\sqrt{\text{Hz}}$, and the fourth one was contaminated and has $6.9 \text{nV}/\sqrt{\text{Hz}}$ noise?

RMS Sum =
$$\sqrt{(2.7)^2 + (2.7)^2 + (2.7)^2 + (6.9)^2}$$
 = 8.33nV/ $\sqrt{\text{Hz}}$

This passes an $8.4 \text{nV}/\sqrt{\text{Hz}}$ spec, yet one of the amplifiers is 64% over the LT1125 spec limit. Clearly, for proper noise measurement, the op amps have to be tested individually.

Competing Quad Op Amp Noise Test Method



PERFORMANCE COMPARISON

The following table summarizes the performance of the LT1124/LT1125 compared to the low cost grades of alternate approaches.

The comparison shows how the specs of the LT1124/LT1125 not only stand up to the industry standard OP-27,

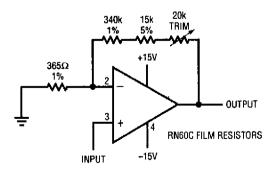
but in most cases are superior. Normally dual and quad performance is degraded when compared to singles, for the LT1124/LT1125 this is not the case.

Guaranteed performance, $V_S = \pm 15V$, $T_A = 25$ °C, low cost devices.

PARAMETER/UN	ITS	LT1124CN8 LT1125CN	OP-27 GP	OP-270 GP	OP-470 GP	UNITS
Voltage Noise, 1k	Hz	4.2 100% Tested	4.5 Sample Tested	– No Limit	5.0 Sample Tested	nV/√Hz
Slew Rate		2.7 100% Tested	1.7 Not Tested	1.7	1.4	V/μs
Gain Bandwidth I	Product	8.0 100% Tested	5.0 Not Tested	No Limit	No Limit	MHz
Offset Voltage	LT1124 LT1125	100 140	100	250 ~	1000	μV μV
Offset Current	LT1124 LT1125	20 30	75 -	20	30	nA nA
Bias Current		30	80	60	60	nA
Supply Current/A	ımp	2.75	5.67	3.25	2.75	mA
Voltage Gain, RL	= 2k	1.5	0.7	0.35	0.4	V/μV
Common Mode F	Rejection Ratio	106	100	90	100	dB
Power Supply Rejection Ratio		110	94	104	105	dB
S8 Package		Yes - LT1124	Yes	No		

TYPICAL APPLICATIONS

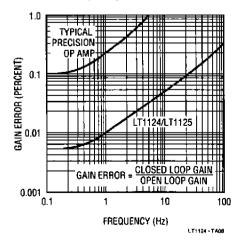
Gain 1000 Amplifier with 0.01% Accuracy, DC to 5Hz



THE HIGH GAIN AND WIDE BANDWIDTH OF THE LT1124/LT1125, IS USEFUL IN LOW FREQUENCY HIGH CLOSED LOOP GAIN AMPLIFIER APPLICATIONS. A TYPICAL PRECISION OP AMP MAY HAVE AN OPEN LOOP GAIN OF ONE MILLION WITH 500kHz BANDWIDTH. AS THE GAIN ERROR PLOT SHOWS, THIS DEVICE IS CAPABLE OF 0.1% AMPLIFYING ACCURACY UP TO 0.3Hz ONLY. EVEN INSTRUMENTATION RANGE SIGNALS CAN VARY AT A FASTER RATE. THE LT1124/LT1125 "GAIN PRECISION — BANDWIDTH PRODUCT" IS 75 TIMES HIGHER, AS SHOWN.

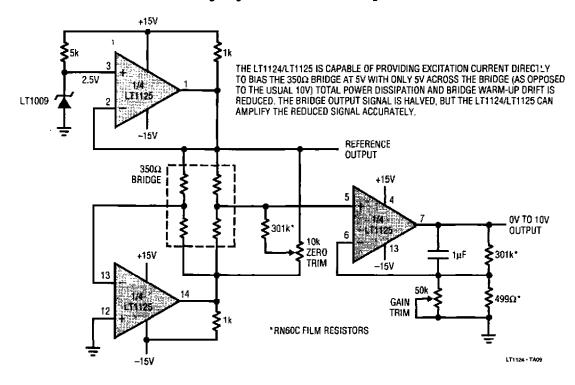
LT1124 - T407

Gain Error vs Frequency Closed Loop Gain = 1000



TYPICAL APPLICATIONS

Strain Gauge Signal Conditioner with Bridge Excitation



SCHEMATIC DIAGRAM (1/2 LT1124, 1/4 LT1125)

